

General Description

The 8205A is the highest performance trench

N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge

for most of the small power switching and

load $\,$ switch applications. The meet the RoHS and

Product requirement with full function reliability approved.



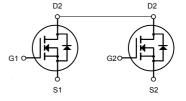
TSSOP-8

General Features

 $V_{DS} = 20V I_{D} = 6A$

 $R_{DS(ON)}$ < 27m Ω @ V_{GS} =4. 5V

 $R_{DS(ON)}$ <37m Ω @ V_{GS} =2. 5V



Application

Battery protection

Load switch

Uninterruptible power supply

Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
8205A	TSSOP-8	8205	5000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V _{DS}	Drain-Source Voltage	20	V	
Vgs	Gate-Source Voltage	±12	V	
I _D	Drain Current-Continuous	6	А	
Ірм	Drain Current-Pulsed (Note 1)	25	А	
P _D	Maximum Power Dissipation	1.5	W	
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	83	°C/W	



Electrical Characteristics (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	21	-	٧
Zero Gate Voltage Drain Current	Ipss	V _{DS} =19.5V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V _{GS} =±10V,V _{DS} =0V	-	_	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.5	0.7	1.2	V
	Rds(on)	V _{GS} =4.5V, I _D =4.5A	-	21	27	mΩ
Drain-Source On-State Resistance		V _{GS} =2.5V, I _D =3.5A	-	27	37	mΩ
Forward Transconductance	grs	V _{DS} =5V,I _D =4.5A	-	10	-	S
Input Capacitance	C _{lss}		-	600	-	PF
Output Capacitance	Coss	V _{DS} =8V,V _{GS} =0V, F=1.0MHz	-	330	-	PF
Reverse Transfer Capacitance	Crss	F-1.UIVIDZ	-	140	-	PF
Turn-on Delay Time	td(on)		-	10	20	nS
Turn-on Rise Time	tr	V _{DD} =10V,I _D =1A	-	11	25	nS
Turn-Off Delay Time	td(off)	$V_{GS}=10V, N_{GEN}=12V$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	35	70	nS
Turn-Off Fall Time	t _f		-	30	60	nS
Total Gate Charge	Qg		-	10	15	nC
Gate-Source Charge	Qgs	V _{DS} =10V,I _D =6A,	-	2.3	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	1.5	-	nC
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V,I _S =1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	1.7	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

Typical Characteristics

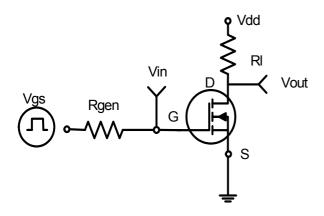


Figure 1:Switching Test Circuit

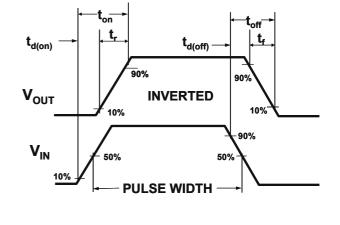


Figure 2:Switching Waveforms

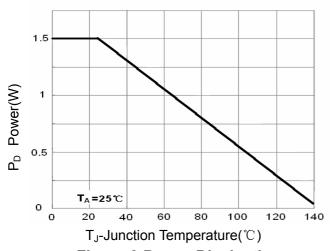


Figure 3 Power Dissipation

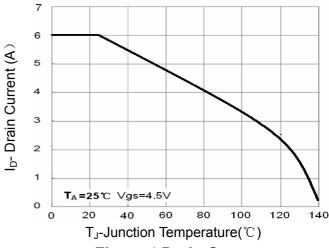


Figure 4 Drain Current

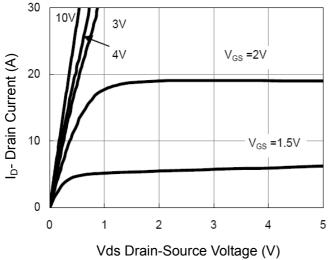


Figure 5 Output Characteristics

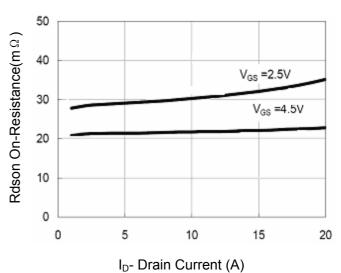


Figure 6 Drain-Source On-Resistance

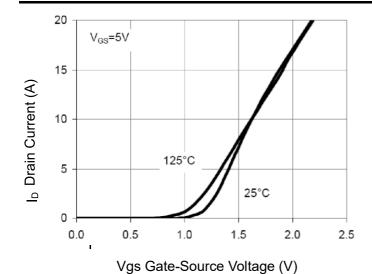
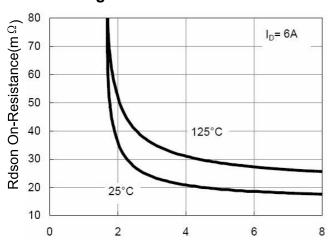


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs

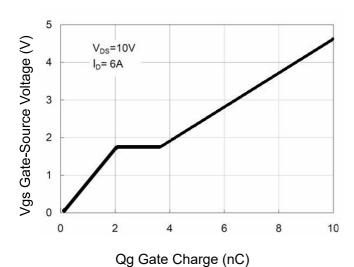
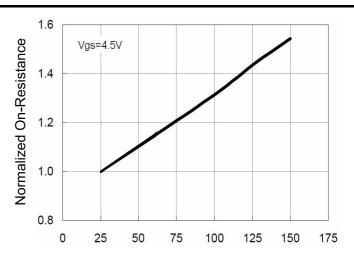
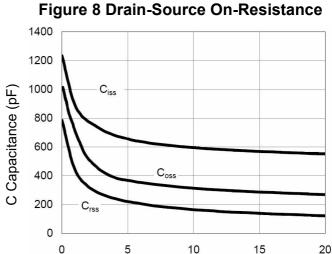


Figure 11 Gate Charge

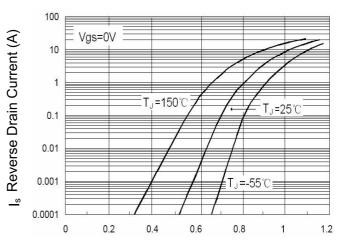


T_J-Junction Temperature(℃)



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward

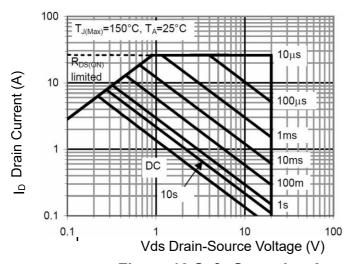


Figure 13 Safe Operation Area

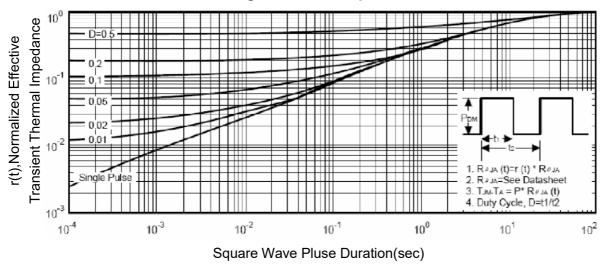
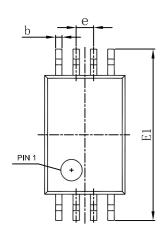
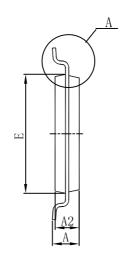


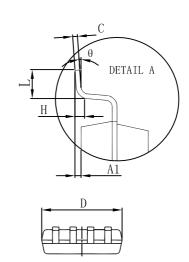
Figure 14 Normalized Maximum Transient Thermal Impedance



TSSOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
D	2.900	3. 100	0. 114	0. 122	
Е	4.300	4. 500	0. 169	0.177	
b	0.190	0.300	0.007	0.012	
c	0.090	0.200	0.004	0.008	
E1	6.250	6. 550	0. 246	0.258	
A		1. 200		0.047	
A2	0.800	1.000	0.031	0.039	
A1	0.050	0. 150	0.002	0.006	
e	0.65 (BSC)		0. 026 (BSC)		
L	0.500	0.700	0.020	0.028	
Н	0.25(TYP)		0.01(TYP)		
θ	1°	7°	1°	7°	



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